SG2M023120J1J

TriQSiC™ 1200V Silicon Carbide Power MOSFET G2

Features

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-
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Benefits

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-
-



Applications

-
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-
-

Table 1 Key performance and package parameters

Type	V_{DS}	I_{DS}	$R_{DS(on),\ typ}$	$T_{J,max}$	Marking	P

Table of contents

Features 1

Benefits 1

Applications 1

Table of contents 2

1 Maximum ratings 3

2 Thermal characteristics 3

3 Electrical characteristics 4

3.1 Static characteristics 4

3.2 Dynamic characteristics 4

3.3 Switching characteristics 5

4 Electrical characteristic diagrams 6

5 Package drawing (TO-263-7L-B) 11

6 Test conditions 12

Revision history 13

Attention 13

1 Maximum ratings

Table 2 Maximum rating

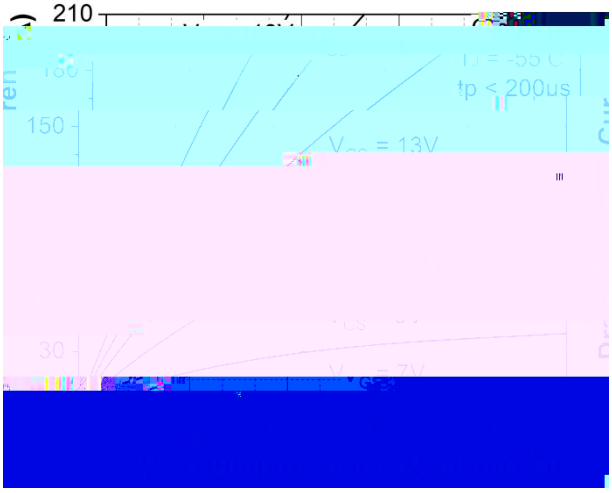
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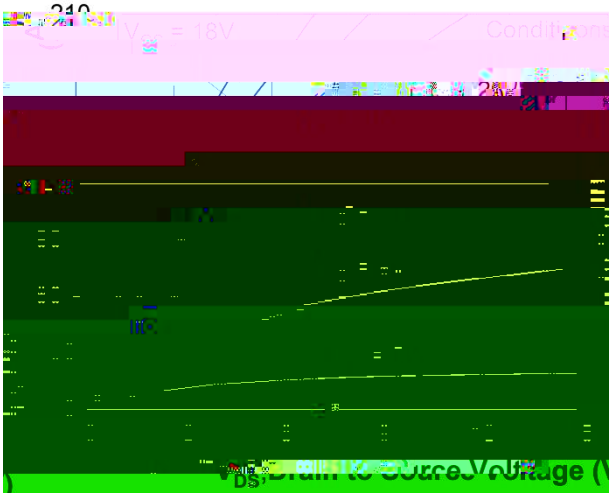
3.3 Switching characteristics

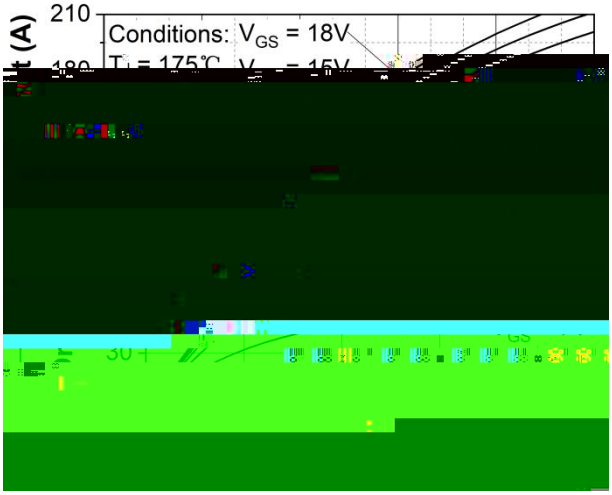
Table 6 Dynamic characteristics

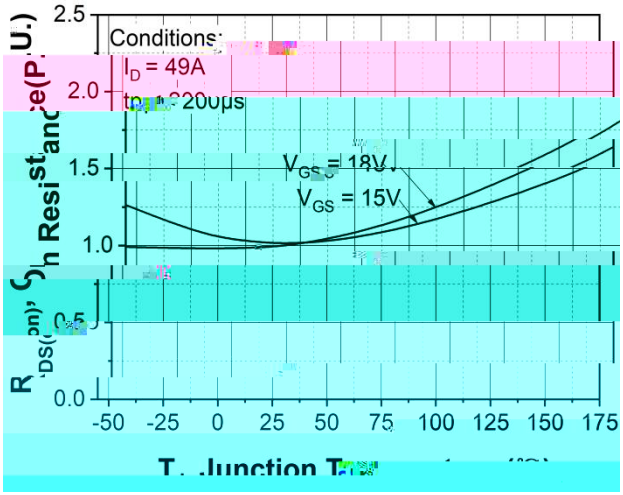
Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note

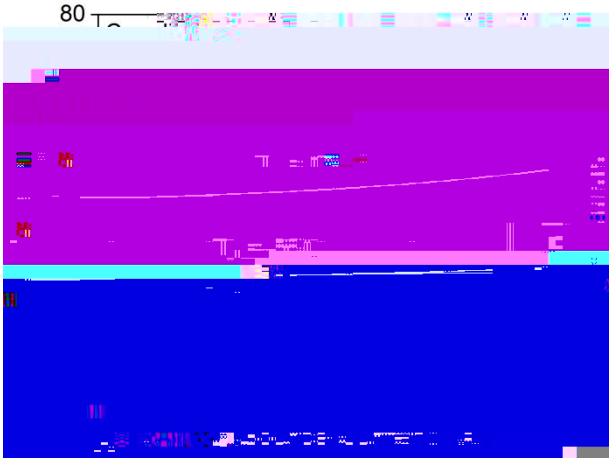
4 Electrical characteristic diagrams

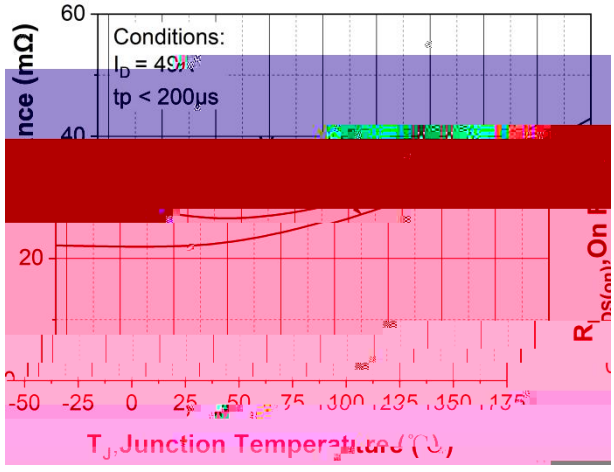




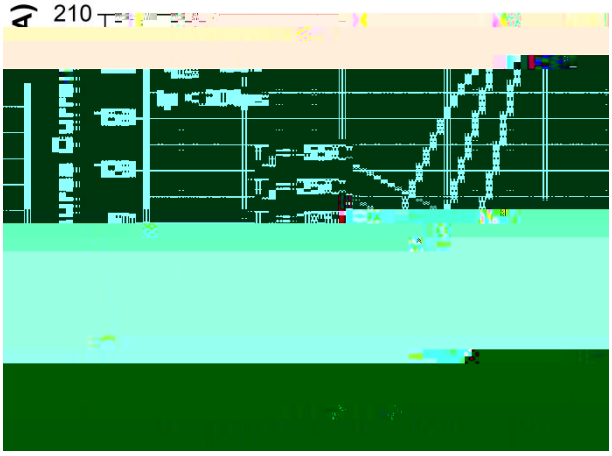


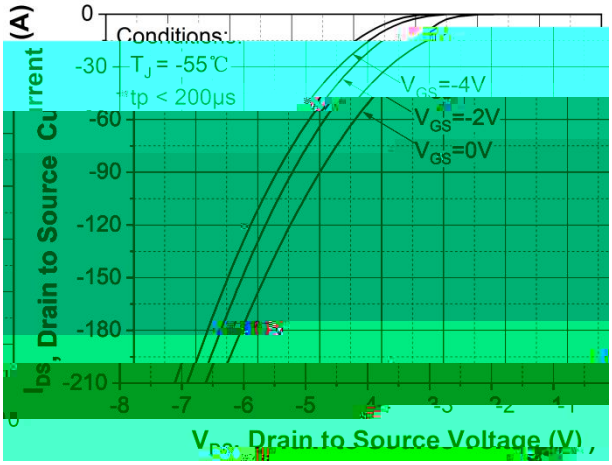


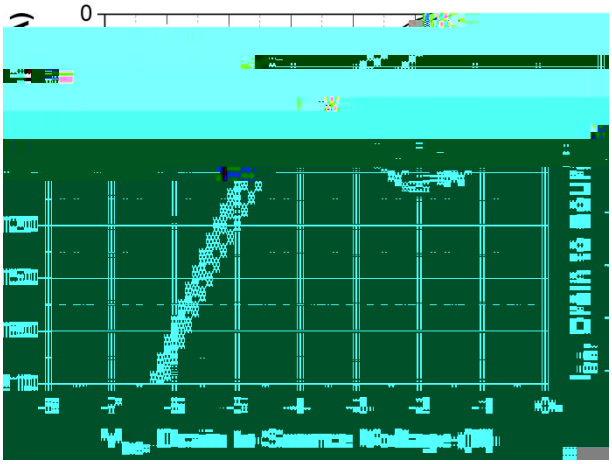


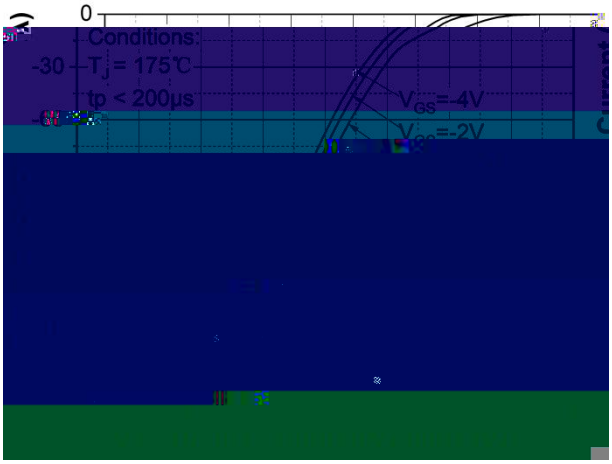


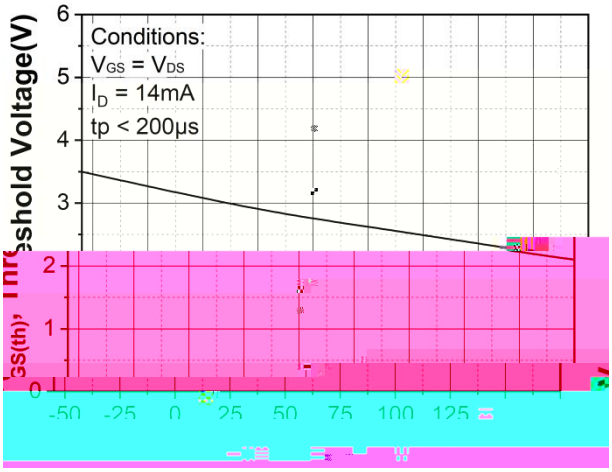
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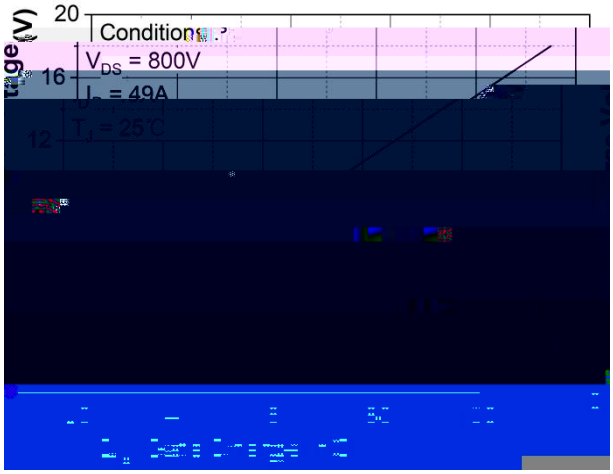








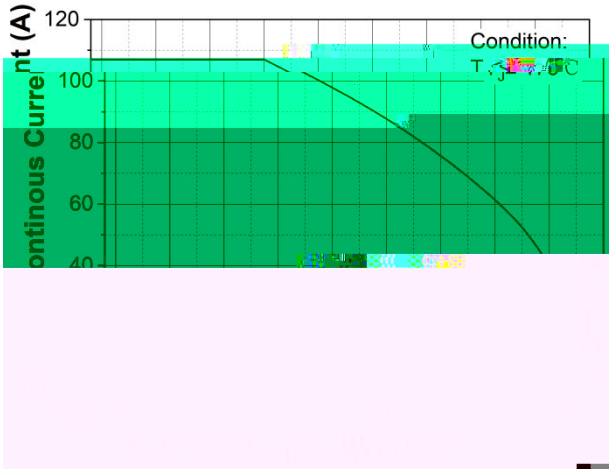


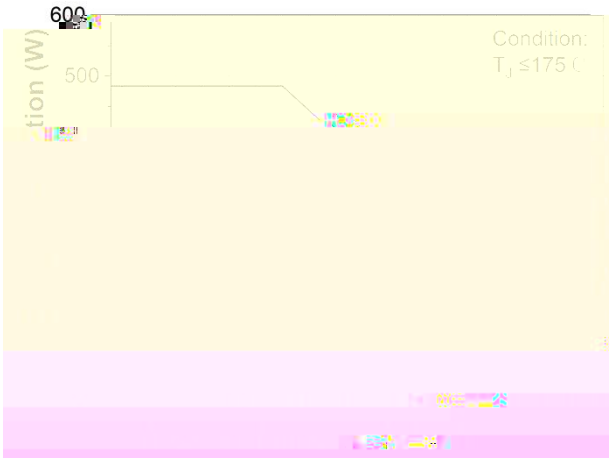


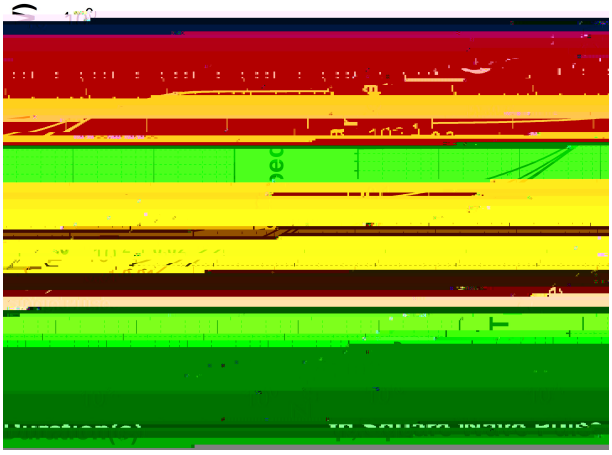
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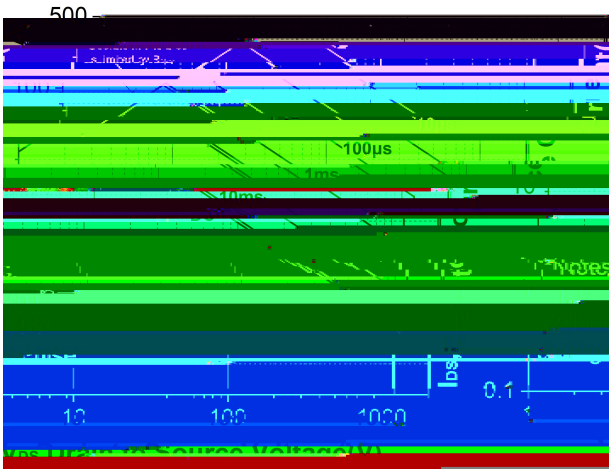
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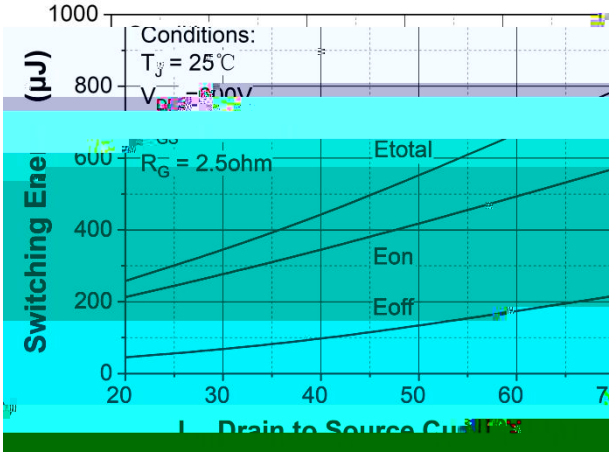
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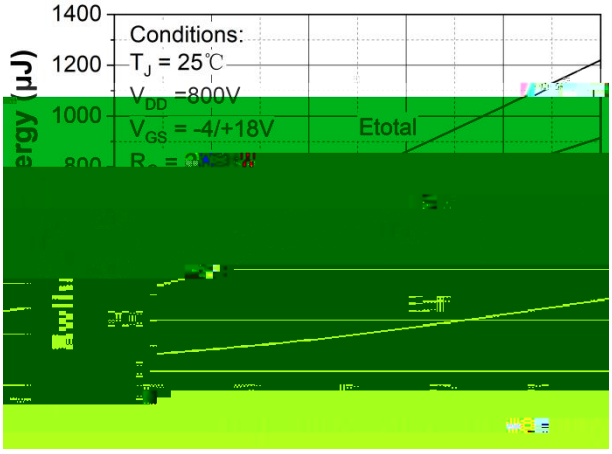




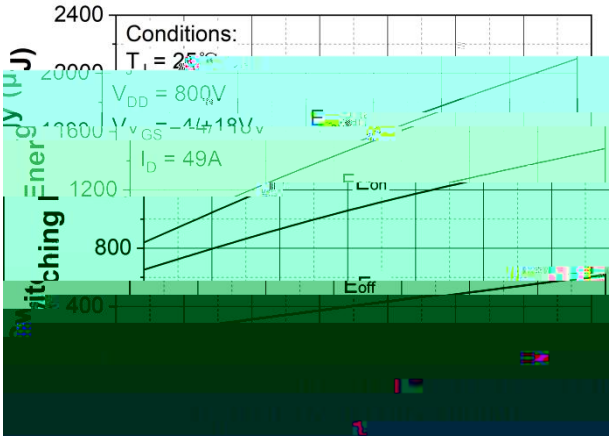


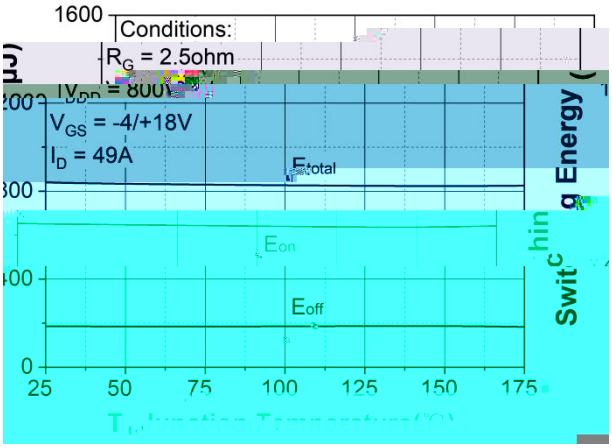


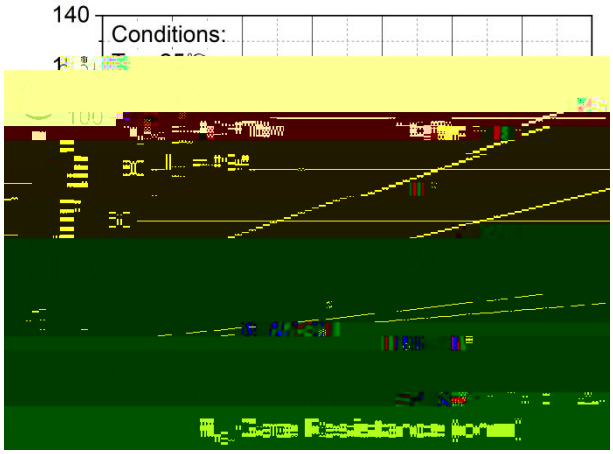




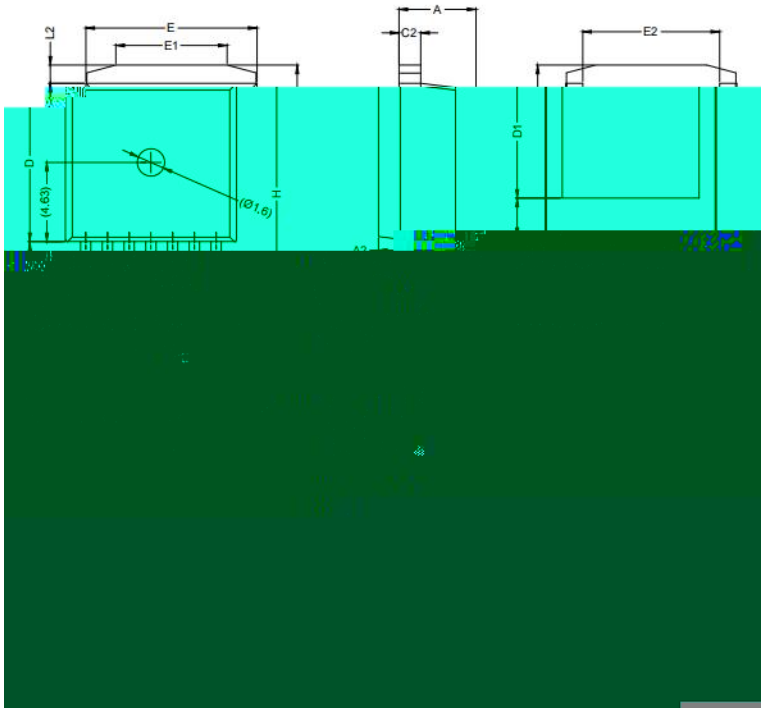
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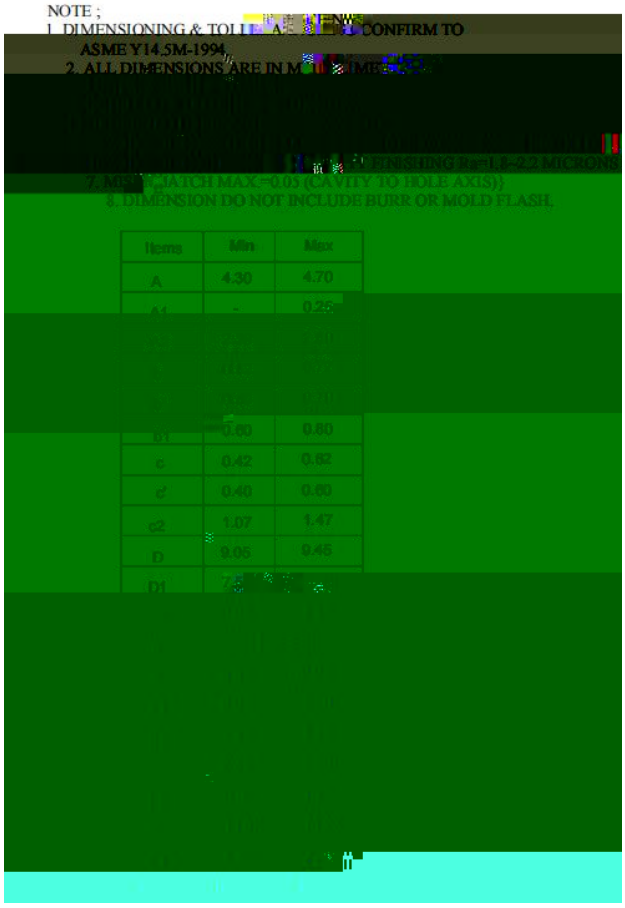




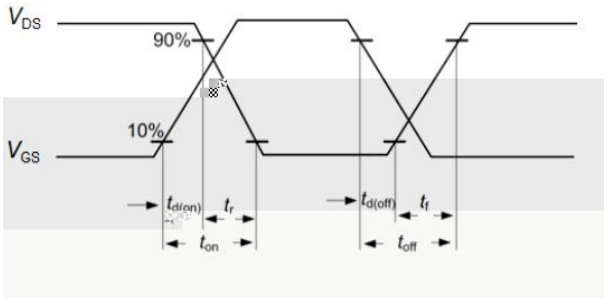


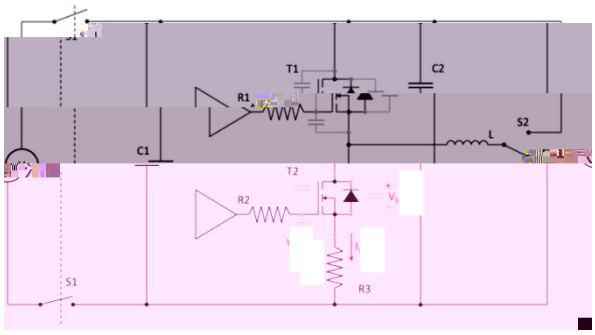
5 Package drawing

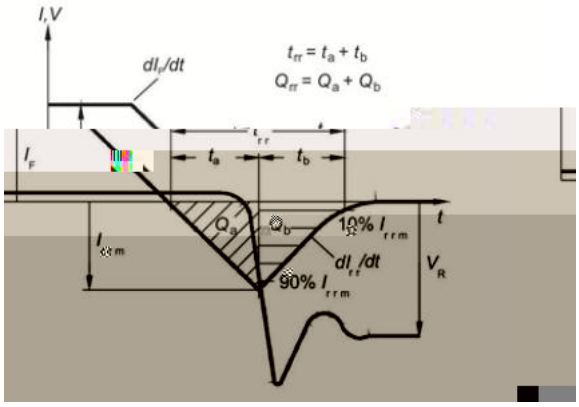




6 Test conditions







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1200V SiC Power MOSFET

Revision history

Document version

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